

Title (en)

GALVANIC BATH, METHOD FOR PRODUCING STRUCTURED HARD CHROMIUM LAYERS AND USE THEREOF

Title (de)

GALVANISCHES BAD UND VERFAHREN ZUR ERZEUGUNG STRUKTURIERTER HARTCHROMSCHICHTEN UND VERWENDUNG

Title (fr)

BAIN GALVANIQUE, PROCEDE PERMETTANT DE PRODUIRE DES COUCHES STRUCTUREES DE CHROME DUR ET UTILISATION DUDIT PROCEDE

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Application

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Abstract (en)

[origin: US6447666B1] The present invention relates to a galvanic bath, to a process for the precipitation of chromium onto objects, and to the use of the process for the generation of textured hard-chrome layers on machine components. The galvanic bath contains in aqueous solution at least one compound delivering chromium(VI)-ions, and it comprises a) chromium(VI)-ions in an amount that corresponds to 100 to 600 g/ltr of chromic acid anhydride, b) sulfate ions in the form of sulfuric acid and/or of a soluble salt thereof in a molar concentration ratio of chromium(VI)-ions to sulfate ions (SO₄-2) ranging from 90:1 to 120:1, and c) 2-hydroxyethane sulfonate ions in an amount that corresponds to 0.01 to 3.0 g/ltr of the sodium salt.

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C25D 1/00

IPC 8 full level

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